

ABSTRACT OF THE INVENTION

The invention relates to discrete, spaced-apart ferroelectric polymer memory device embodiments. The ferroelectric polymer memory device is fabricated by spin-on polymer processing and etching using photolithographic technology. The size of the discrete, spaced-apart ferroelectric polymer structures may be tied to a specific photolithography minimum feature dimension.

The invention also relates to a process for making embodiments of a polymer memory device that includes discrete, spaced-apart ferroelectric polymer structures. The discrete, spaced-apart ferroelectric polymer structures may have a minimum feature that is tied to the current photolithography that may reduce the voltage and increase the switching speed.

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